

Full - Bridge NPT IGBT Power Module

$$V_{CES} = 1200V$$

$$I_C = 150A @ T_c = 80^{\circ}C$$

Application

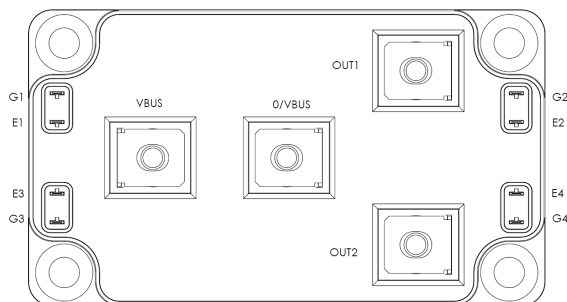
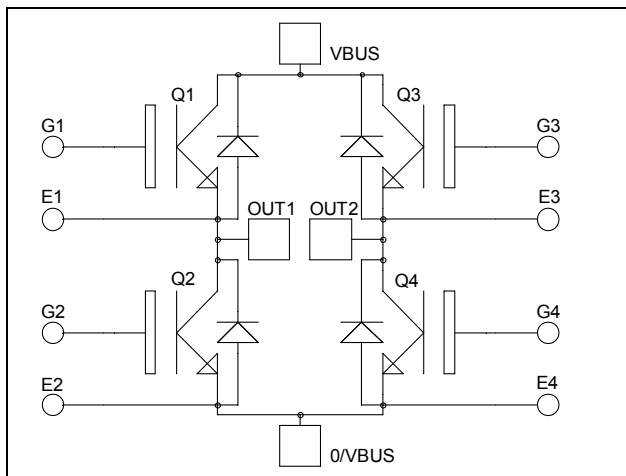
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^{\circ}C$	200
		$T_c = 80^{\circ}C$	150
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	300
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	961
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	300A @ 1200V



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $V_{CE} = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			350 600	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 150A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		3.2 3.9	3.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 5\text{ mA}$		4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$				± 500	nA

Dynamic Characteristics

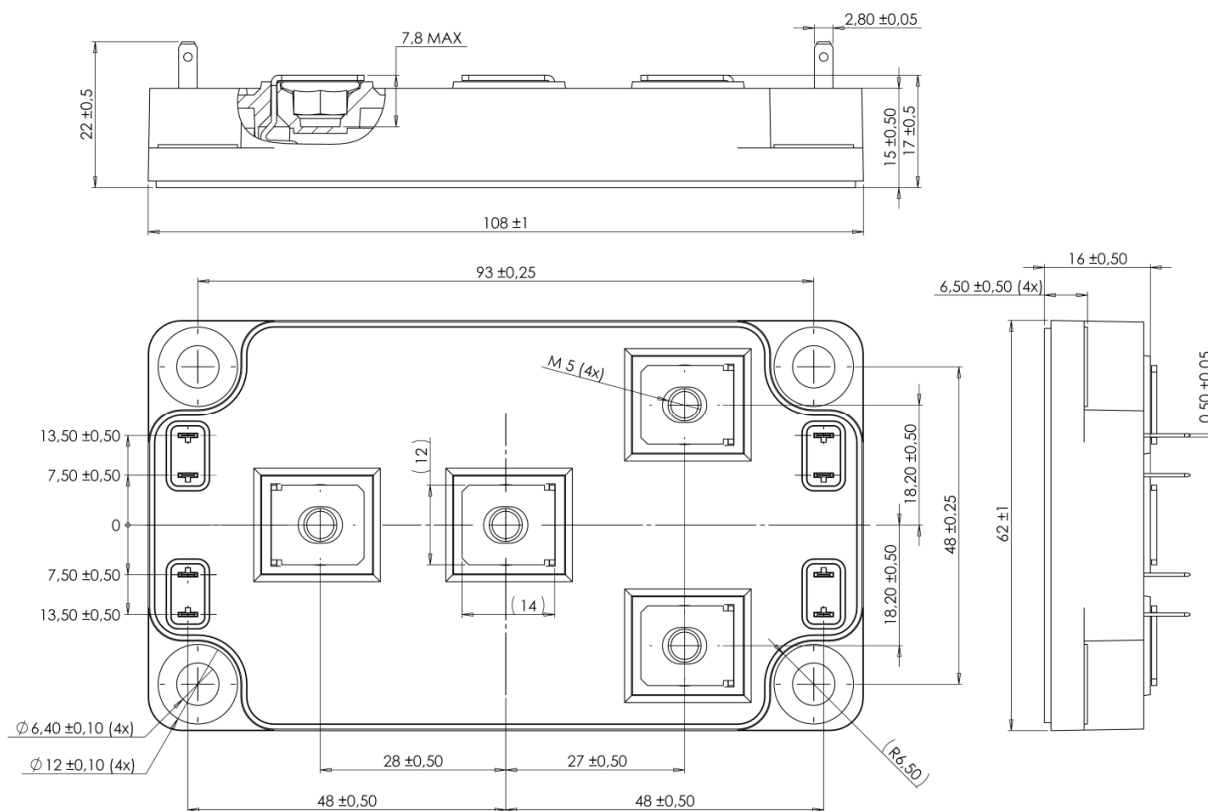
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$			10.2		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$			1.4		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$			0.75		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 5.6\Omega$			120		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				310		
T_f	Fall Time				20		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 5.6\Omega$			130		ns
T_r	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				360		
T_f	Fall Time				30		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 5.6\Omega$	$T_j = 125^\circ\text{C}$		18		mJ
E_{off}	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$		8		

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			350 600	μA
I_F	DC Forward Current		$T_c = 85^\circ\text{C}$		150		A
V_F	Diode Forward Voltage	$I_F = 150A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		2.1 1.9		V
t_{rr}	Reverse Recovery Time	$I_F = 150A$ $V_R = 600V$ $di/dt = 3600A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		120		ns
			$T_j = 125^\circ\text{C}$		210		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		11		μC
			$T_j = 125^\circ\text{C}$		28		
E_r	Reverse recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		3.6 9		mJ

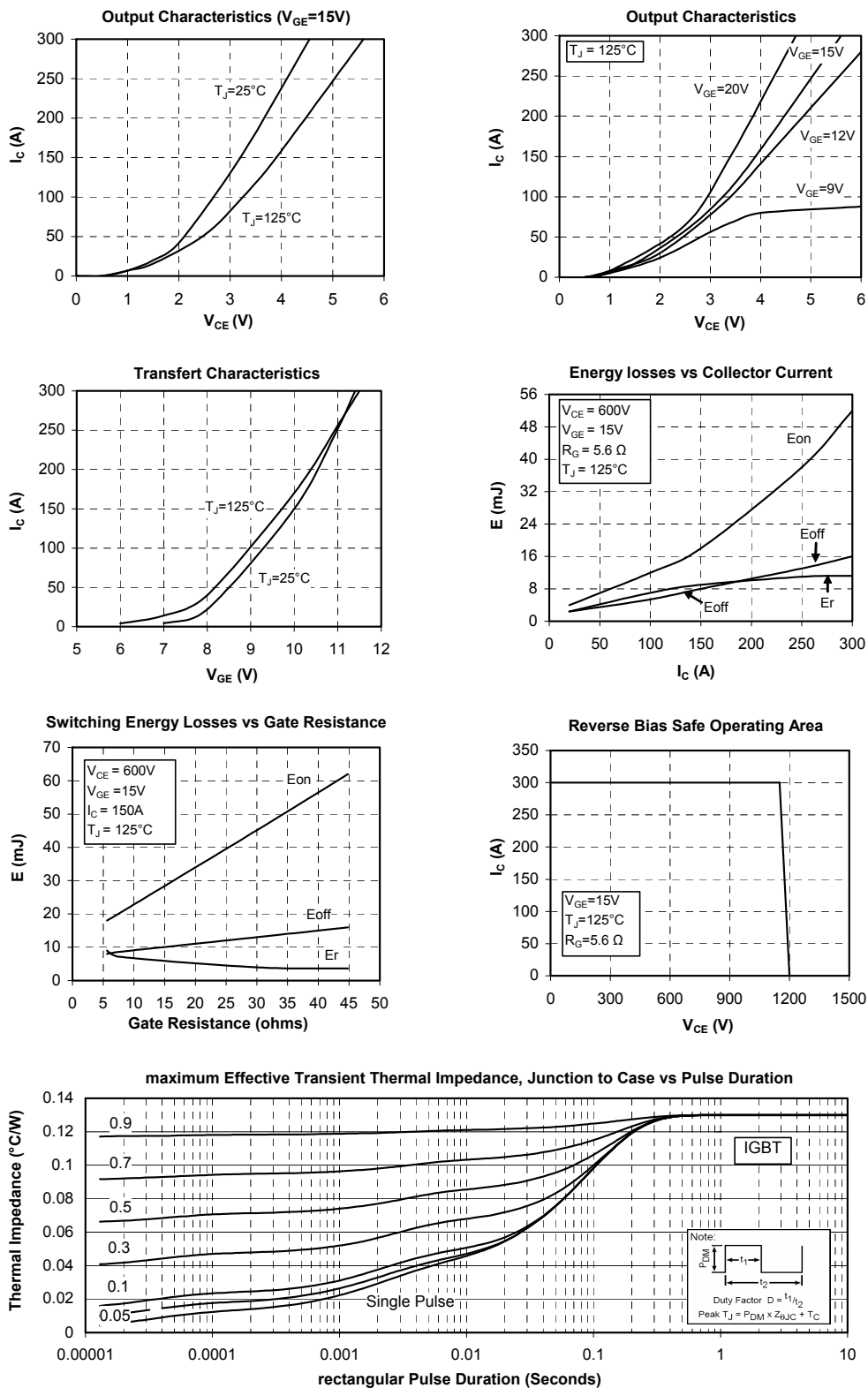
Thermal and package characteristics

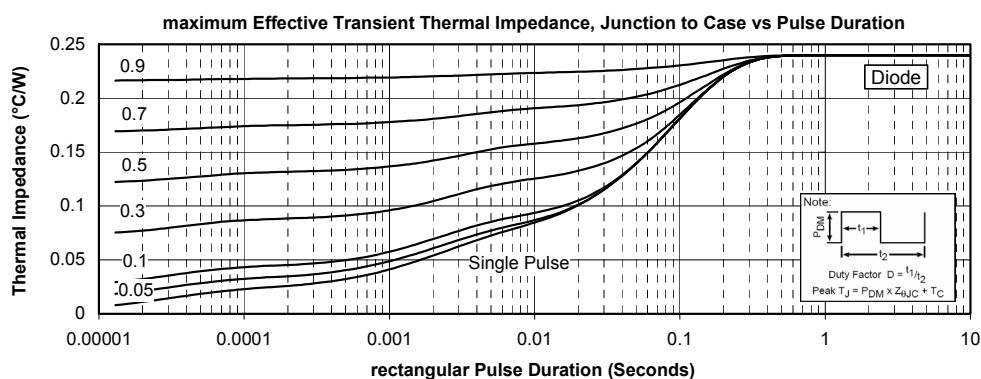
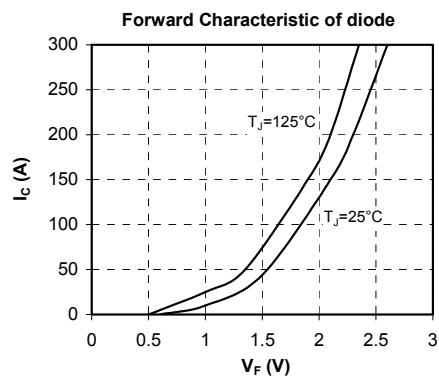
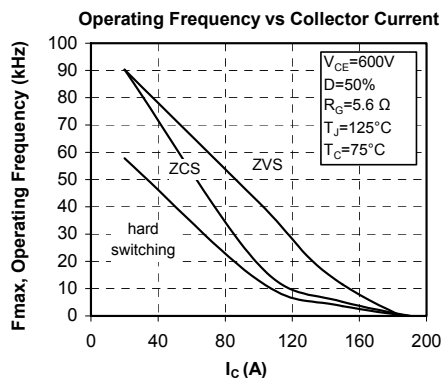
Symbol	Characteristic		Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.13	°C/W
		Diode			0.24	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz		4000			V
T _J	Operating junction temperature range		-40		150	°C
T _{STG}	Storage Temperature Range		-40		125	
T _C	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				300	g

SP6 Package outline (dimensions in mm)


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve





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